# **SWITCHMODE** <sup>™</sup> **Power Rectifier**

This SWITCHMODE power rectifier uses the Schottky Barrier principle with a platinum barrier metal. This state-of-the-art device has the following features:

#### **Features**

- Low Forward Voltage
- 175°C Operating Junction Temperature
- Low Power Loss/High Efficiency
- High Surge Capacity
- This is a Pb-Free Device

#### **Applications**

- Power Supply Output Rectification
- Power Management

#### **Mechanical Characteristics**

- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 1.7 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds



#### ON Semiconductor®

http://onsemi.com

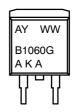
### SCHOTTKY BARRIER RECTIFIER 10 AMPERES, 60 VOLTS





D<sup>2</sup>PAK CASE 418B STYLE 3

#### **MARKING DIAGRAM**



A = Assembly Location

Y = Year
WW = Work Week
B1060 = Device Code
G = Pb-Free Package
AKA = Diode Polarity

#### **ORDERING INFORMATION**

| Device       | Package                         | Shipping <sup>†</sup> |
|--------------|---------------------------------|-----------------------|
| NRVBB1060T4G | D <sup>2</sup> PAK<br>(Pb-Free) | 800/Tape & Reel       |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

#### **MAXIMUM RATINGS**

| Rating  | Symbol   | Value       | Unit |
|---|--|-------------|------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage                        | V <sub>RRM</sub><br>V <sub>RWM</sub><br>V <sub>R</sub> | 60          | V    |
| Average Rectified Forward Current (Rated V <sub>R</sub> ) T <sub>C</sub> = 133°C                        | I <sub>F(AV)</sub>                                     | 10          | Α    |
| Peak Repetitive Forward Current<br>(Rated V <sub>R</sub> , Square Wave, 20 kHz) T <sub>C</sub> = 133°C  |  | 20          | Α    |
| Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz) | I <sub>FSM</sub>                                       | 150         | Α    |
| Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)   |  | 0.5         | Α    |
| Operating Junction Temperature (Note 1)   |  | -65 to +175 | °C   |
| Storage Temperature   |  | -65 to +175 | °C   |
| Voltage Rate of Change (Rated V <sub>R</sub> )  |  | 10,000      | V/μs |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### THERMAL CHARACTERISTICS

| Maximum Thermal Resistance, Junction-to-Case  |                 | 2.0                        | °C/W |  |
|---|-----------------|----------------------------|------|--|
| Maximum Thermal Resistance, Junction-to-Ambient   | $R_{\theta JA}$ | 60                         | °C/W |  |
| ELECTRICAL CHARACTERISTICS  |                 |                            |      |  |
| Maximum Instantaneous Forward Voltage (Note 2) $ \begin{aligned} &(i_F=10 \text{ Amps, } T_C=125^\circ\text{C}) \\ &(i_F=10 \text{ Amps, } T_C=25^\circ\text{C}) \\ &(i_F=20 \text{ Amps, } T_C=125^\circ\text{C}) \\ &(i_F=20 \text{ Amps, } T_C=25^\circ\text{C}) \end{aligned} $ | VF              | 0.7<br>0.8<br>0.85<br>0.95 | V    |  |

 $i_R$ 

mΑ

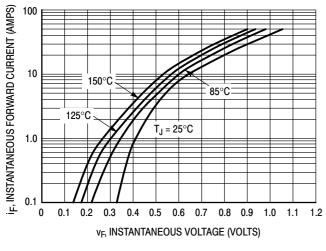
25 0.10

Maximum Instantaneous Reverse Current (Note 2)

(Rated dc Voltage,  $T_C$  = 125°C) (Rated dc Voltage,  $T_C$  = 25°C)

<sup>1.</sup> The heat generated must be less than the thermal conductivity from Junction-to-Ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ .

<sup>2.</sup> Pulse Test: Pulse Width = 300  $\mu$ s, Duty Cycle  $\leq$  2.0%.



100

T<sub>J</sub> = 150°C

10

125°C

1.0

85°C

0.01

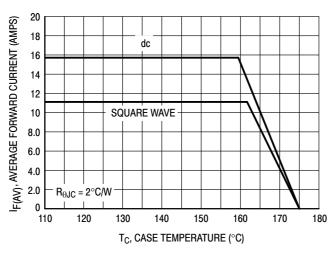
0.001

0 10 20 30 40 50 60

V<sub>R</sub>, REVERSE VOLTAGE (VOLTS)

Figure 1. Typical Forward Voltage

**Figure 2. Typical Reverse Current** 



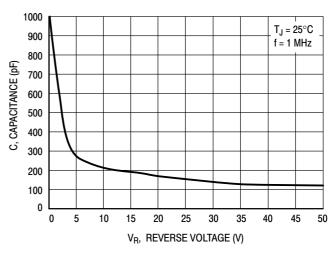
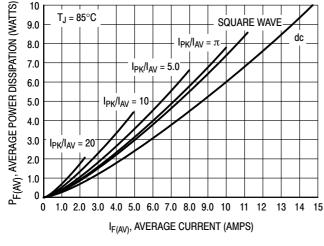


Figure 3. Current Derating, Case

Figure 4. Typical Capacitance



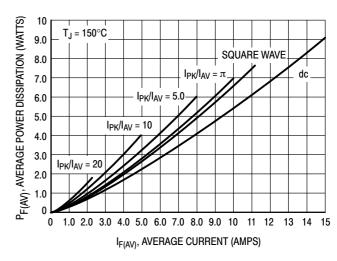


Figure 5. Typical Forward Power Dissipation

Figure 6. Typical Forward Power Dissipation

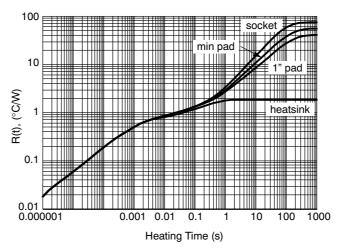
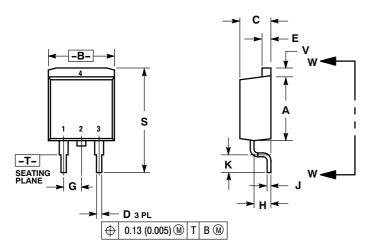
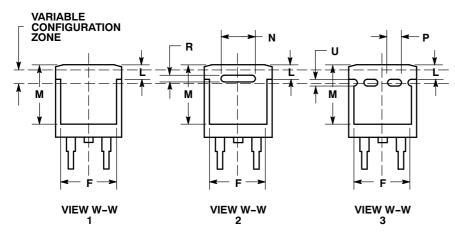


Figure 7. Single-Pulse Transient Response Curves, Various Mounting Conditions

#### **PACKAGE DIMENSIONS**

#### D<sup>2</sup>PAK 3 CASE 418B-04 **ISSUE J**





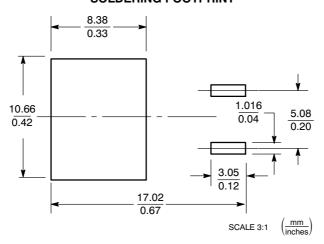
#### NOTES:

- NO LES:
  1. DIMENSIONING AND TOLERANCING
  PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. 4188-01 THRU 418B-03 OBSOLETE,
  NEW STANDARD 418B-04.

|     | INCHES    |       | MILLIMETERS |       |  |
|-----|-----------|-------|-------------|-------|--|
| DIM | MIN       | MAX   | MIN         | MAX   |  |
| Α   | 0.340     | 0.380 | 8.64        | 9.65  |  |
| В   | 0.380     | 0.405 | 9.65        | 10.29 |  |
| С   | 0.160     | 0.190 | 4.06        | 4.83  |  |
| D   | 0.020     | 0.035 | 0.51        | 0.89  |  |
| Е   | 0.045     | 0.055 | 1.14        | 1.40  |  |
| F   | 0.310     | 0.350 | 7.87        | 8.89  |  |
| G   | 0.100 BSC |       | 2.54 BSC    |       |  |
| Н   | 0.080     | 0.110 | 2.03        | 2.79  |  |
| J   | 0.018     | 0.025 | 0.46        | 0.64  |  |
| K   | 0.090     | 0.110 | 2.29        | 2.79  |  |
| L   | 0.052     | 0.072 | 1.32        | 1.83  |  |
| M   | 0.280     | 0.320 | 7.11        | 8.13  |  |
| N   | 0.197 REF |       | 5.00 REF    |       |  |
| Р   | 0.079 REF |       | 2.00 REF    |       |  |
| R   | 0.039 REF |       | 0.99 REF    |       |  |
| S   | 0.575     | 0.625 | 14.60       | 15.88 |  |
| V   | 0.045     | 0.055 | 1.14        | 1.40  |  |

# STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SWITCHMODE is a trademark of Semiconductor Components Industries, LLC.

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

#### **PUBLICATION ORDERING INFORMATION**

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81-3-5773-3850 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative